

Fig. 1

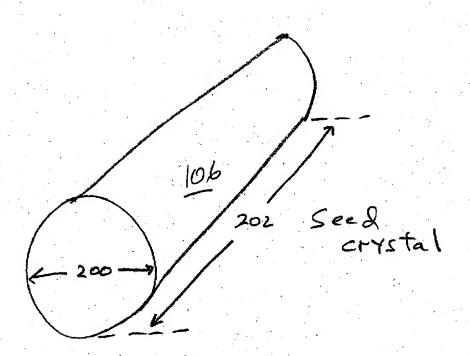


Fig. 2

100 K

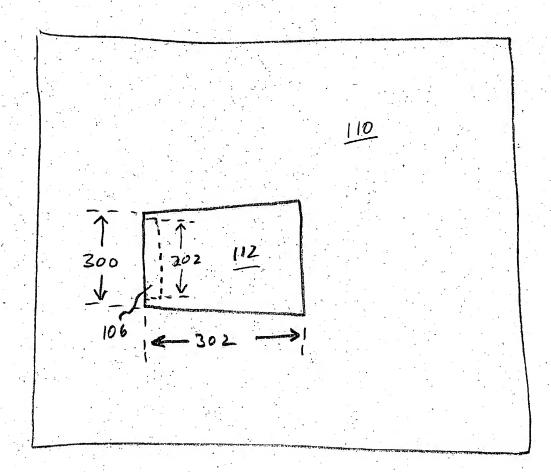


Fig. 3

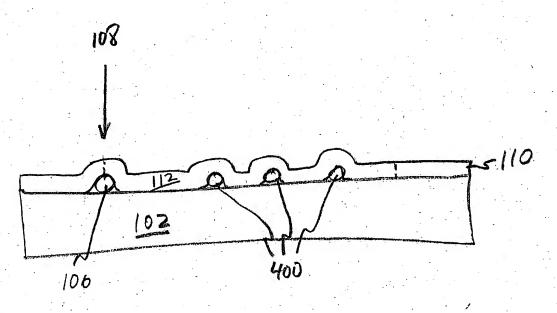
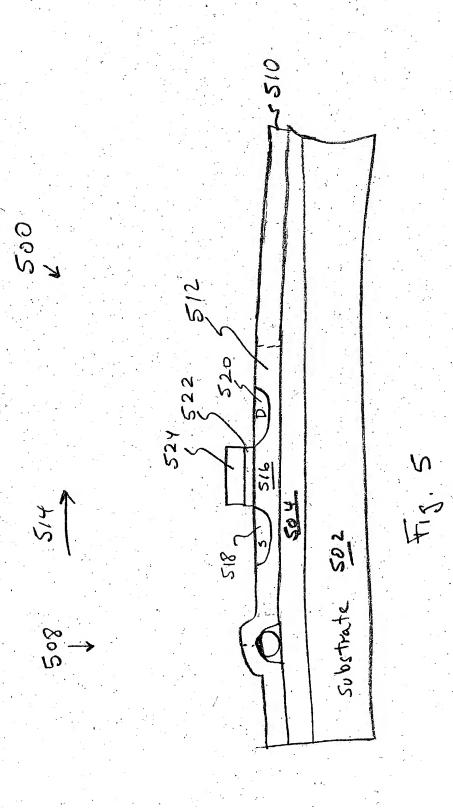
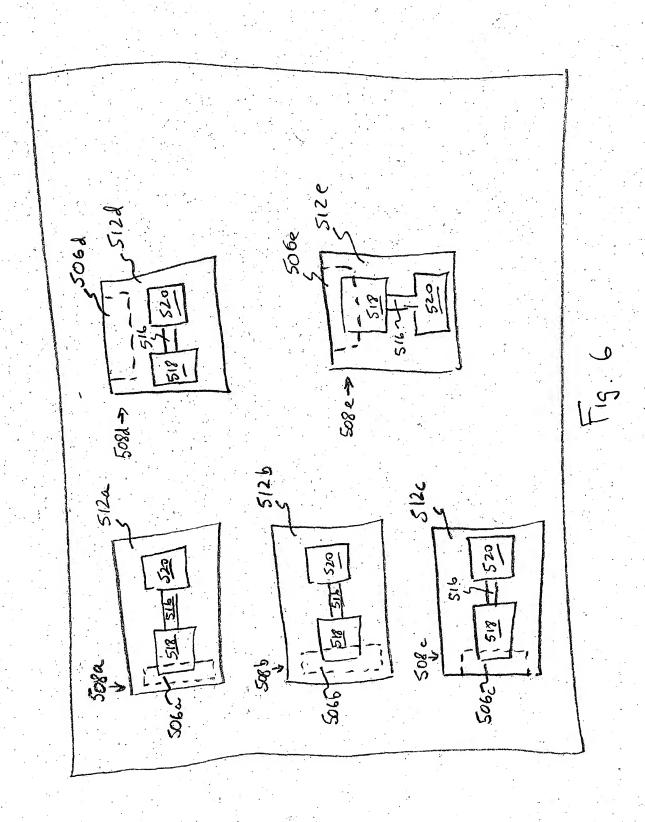
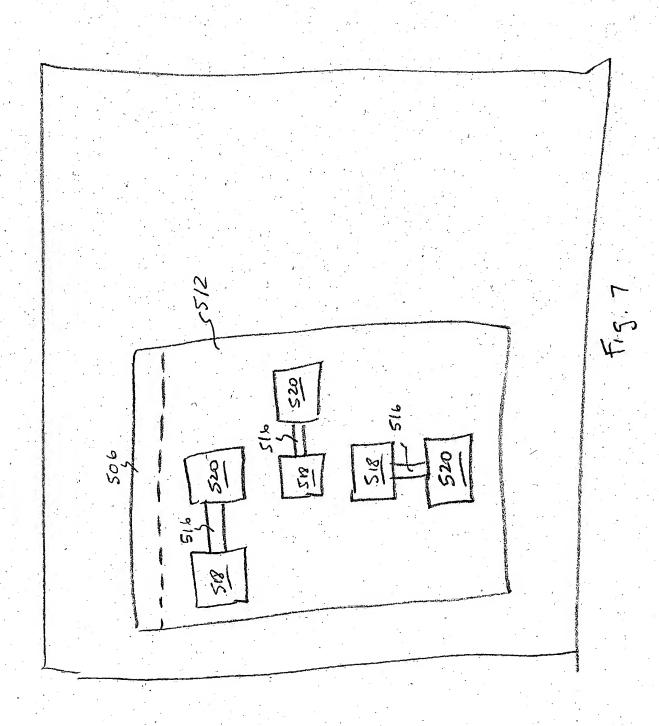


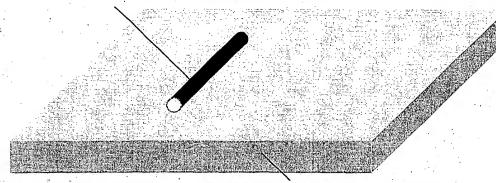
Fig. 4





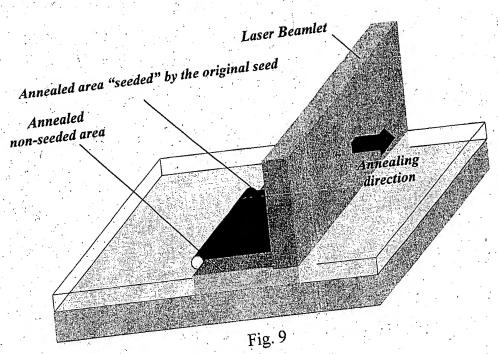


Semiconductor "seed" (i.e. Si nanowire: ~10nm dia, ~100um length)



Substrate (w/ or w/o additional coatings)

Fig. 8



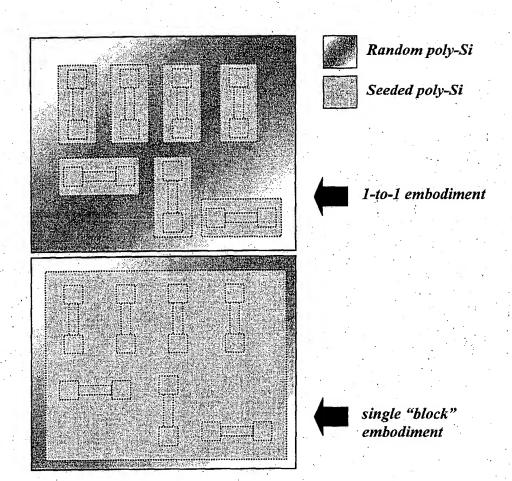


Fig. 10

START forming substrate 1= 1102 Forming insulator film \$ 1103 torming single-crystal seed 41106 torming amorphous film annealing 5 1108 51110 forming single-crystal domain torming pixel areas [1112

Fig. 11